
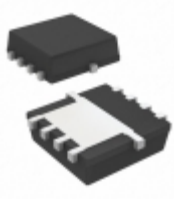


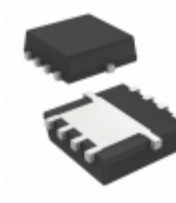




	<h2>SI7726DN-T1-GE3</h2>
	<p><b>Hersteller-Teilenummer:</b> SI7726DN-T1-GE3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 35A 1212-8</p> <p><b>Datenblätter:</b>  SI7726DN-T1-GE3.pdf</p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 37054 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SI7726DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 35A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	37054 pcs Stock
detaillierte Beschreibung	N-Channel 30V 35A (Tc) 3.8W (Ta), 52W (Tc) Surface
Serie	SkyFET®, TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-50°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.8W (Ta), 52W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	9.5 mOhm @ 10A, 10V
VGS (th) (Max) @ Id	2.6V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	43nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1765pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7726DN-T1-GE3TR

SI7726DN-T1-GE3 ist neu im Original, Suche SI7726DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7726DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7726DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SI7726DN-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 35A 1212-8</p>	 <p><b>SI7726DN</b> VB SI7726DN VB</p>	 <p><b>SI7732DP-T1-E3</b> VISHAY VISHAY SO-8</p>	 <p><b>SI7720DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 12A 1212-8</p>
 <p><b>SI7726DN-T1-E3</b> VISHAY SI7726DN-T1-E3 VISHAY</p>	 <p><b>SI7732DP-T1-GE3</b> Vishay Precision Group SI7732DP-T1-GE3 VISHAY</p>	 <p><b>SI7738DP-T1-3</b> Vishay Precision Group SI7738DP-T1-3 VISHAY</p>	 <p><b>SI7720DN-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 12A 1212-8</p>

### heiße Teile

Mehr

SI7686DP-T1-E3	SI7686DP-T1-GE3	SI7686DP-T1-GE3	SI7703DN	SI7703EDN
SI7703EDN-T1	SI7703EDN-T1-E3	SI7703EDN-T1-E3	SI7703EDN-T1-GE3	SI7703EDN-T1-GE3
SI7703EDN-TI-E3	SI7705DN	SI7705DN-T1	SI7705DN-T1-E3	SI7716ADN
SI7716ADN-T1-E3	SI7716ADN-T1-GE3	SI7716ADN-T1-GE3	SI7716ADN-TI-GE3	SI7716DN-T1-GE3
SI7720DN-T1-E3	SI7720DN-T1-GE3	SI7720DN-T1-GE3	SI7726DN	SI7726DN-T1-E3
SI7726DN-T1-GE3	SI7732DP-T1-GE3	SI7738DP	SI7738DP-T1-3	SI7738DP-T1-E3
SI7738DP-T1-E3	SI7738DP-T1-GE3	SI7738DP-T1-GE3	SI7742DP-T1-E3	SI7742DP-T1-GE3
SI7742DP-T1-GE3	SI7748DP-T1-GE3	SI7748DP-T1-GE3	SI7758DP	SI7758DP-T1-GE3
SI7758DP-T1-GE3	SI7772DP-T1-GE3	SI7772DP-T1-GE3	SI7774DP-T1-GE3	SI7774DP-T1-GE3
SI7784DP-T1-GE3	SI7784DP-T1-GE3	SI7788DP-T1-GE3	SI7788DP-T1-GE3	SI7790DP-T1-E3

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